

a second nitride based semiconductor layer, formed on said first nitride based semiconductor layer in said striped opening, including a second conductivity type cladding layer and containing at least one of boron, aluminum, gallium, indium and thallium, wherein

*B' Cont'd*

    said current blocking layer includes a multilayer structure of at least one first layer of a nitride based semiconductor containing at least one of aluminum and boron and at least one second layer of a nitride based semiconductor containing indium and having a smaller band gap than said first layer.

**2. (Amended)** The semiconductor laser device according to claim 1, wherein

    said at least one first layer of a nitride based semiconductor has a larger aluminum composition ratio than that of said at least one second layer of a nitride based semiconductor or a larger boron composition ratio than that of said at least one second layer of a nitride based semiconductor, and

    said at least one second layer of a nitride based semiconductor has a larger indium composition ratio than that of said at least one first layer of a nitride based semiconductor.

*Det Cl*

**3. (Amended)** The semiconductor laser device according to claim 1, wherein

    said first nitride based semiconductor layer further includes a second conductivity type cladding layer provided between said active layer and a second conductivity type second conductivity type cladding layer in said second nitride based semiconductor layer.